

2SA2188

FOR GENERAL PURPOSE HIGH CURRENT DRIVE APPLICATION
SILICON PNP EPITAXIAL TYPE

DESCRIPTION

ISAHAYA 2SA2188 is a silicon PNP epitaxial type transistor designed with high collector current, low $V_{CE(sat)}$.

FEATURE

- High collector current

$$I_{C(MAX)} = -650\text{mA}$$

- Low collector to emitter saturation voltage

$$V_{CE(sat)} < -0.7V_{max}$$

APPLICATION

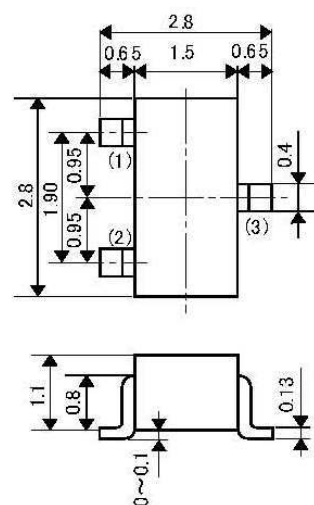
For switching application, small type motor drive application.

MAXIMUM RATINGS ($T_a=25^\circ\text{C}$)

記号	項目	定格値	単位
V_{CEO}	Collector to Emitter voltage	-20	V
V_{CBO}	Collector to Base voltage	-25	V
V_{EBO}	Emitter to Base voltage	-4	V
I_{CM}	Peak collector current	-1000	mA
I_C	Collector current	-650	mA
P_C	Collector dissipation	200	mW
T_j	Junction temperature	150	$^\circ\text{C}$
T_{stg}	Storage temperature	-55~150	$^\circ\text{C}$

OUTLINE DRAWING

Unit : mm

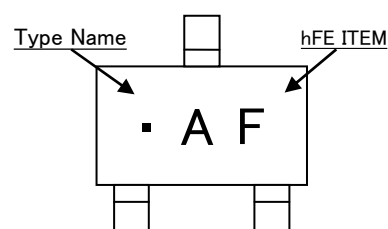


Notice: The dimension without tolerance represent central value.

TERMINAL CONNECTOR

- ① : BASE EIAJ : SC-59
- ② : EMITTER JEDEC : TO-236
- ③ : COLLECTOR Resemblance

MARKING



ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$)

Symbol	Parameter	Test condition	Limits			Unit
			Min	Typ	Max	
$V_{(BR)CEO}$	C to E break down voltage	$I_C = -100\mu\text{A}$, $I_B = 0$	-20			V
$V_{(BR)CBO}$	C to B break down voltage	$I_C = -10\mu\text{A}$, $I_E = 0$	-25			V
$V_{(BR)EBO}$	E to B break down voltage	$I_E = -10\mu\text{A}$, $I_C = 0$	-4			V
I_{CBO}	Collector cut off current	$V_{CB} = -25\text{V}$, $I_E = 0$			-1	μA
I_{EBO}	Emitter cut off current	$V_{EB} = -2\text{V}$, $I_C = 0$			-1	μA
h_{FE}^*	DC forward current gain	$I_C = -100\text{mA}$, $V_{CE} = -4\text{V}$	150		800	---
$V_{CE(sat)}$	C to E saturation voltage	$I_C = -500\text{mA}$, $I_B = -25\text{mA}$		-0.3	-0.7	V
f_T	Gain band width product	$I_E = 10\text{mA}$, $V_{CE} = -6\text{V}$, $f = 100\text{MHz}$		210		MHz

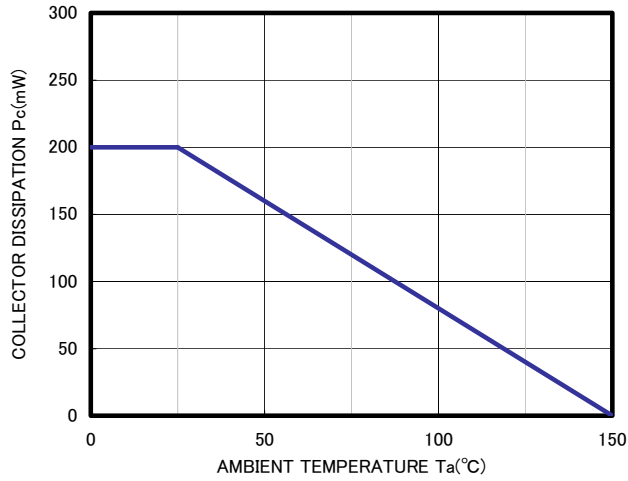
*: It shows hFE classification in below table.

Marking	•AE	•AF	•AG
hFE	150~300	250~500	400~800

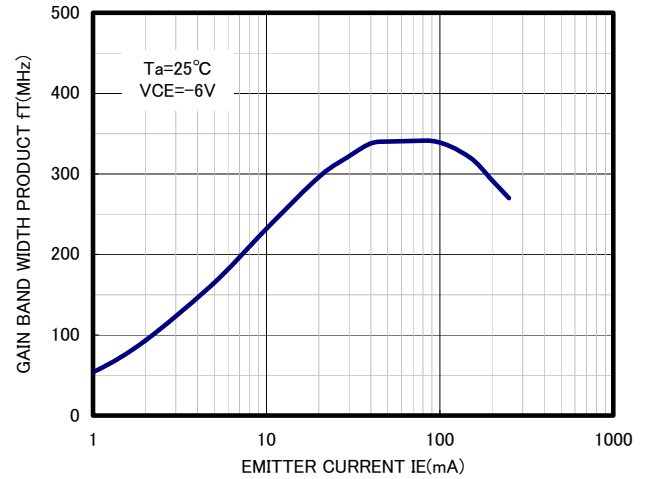
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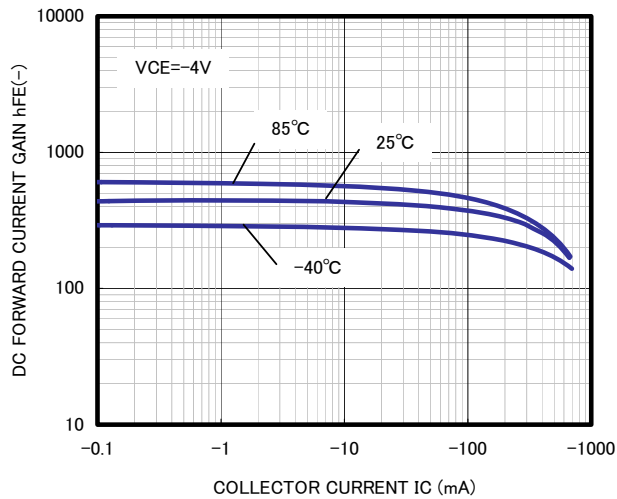
COLLECTOR DISSIPATION VS. AMBIENT TEMPERATURE



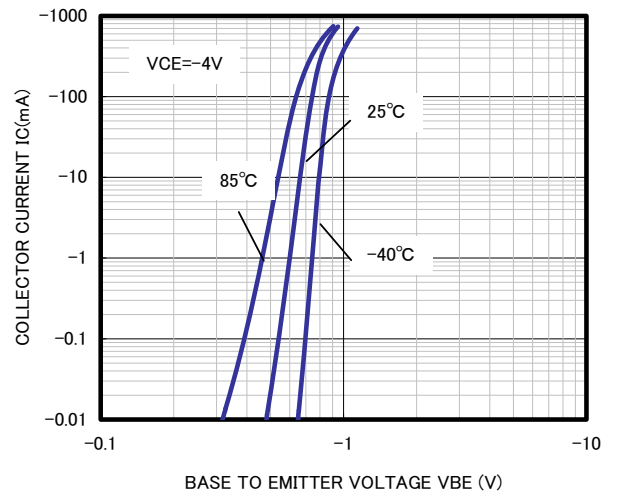
GAIN BAND WIDTH PRODUCT VS. EMITTER CURRENT



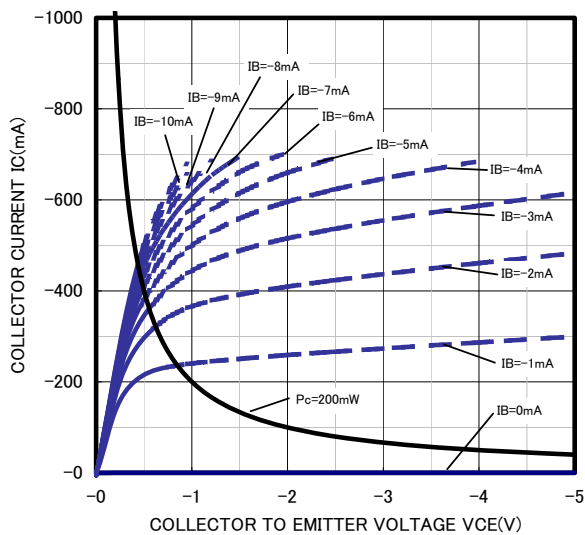
DC FORWARD CURRENT GAIN VS. COLLECTOR CURRENT



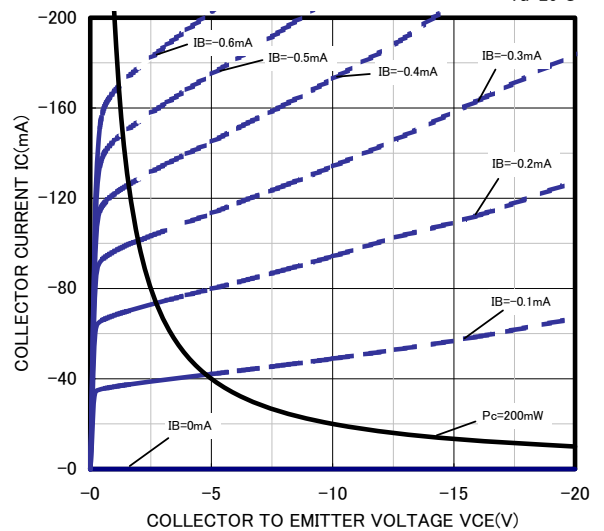
COMMON EMITTER TRANSFER



COMMON EMITTER OUTPUT(1) $T_a=25^\circ\text{C}$



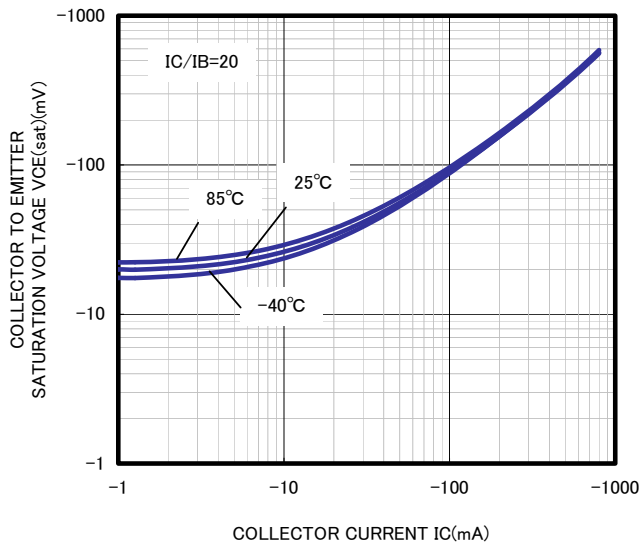
COMMON EMITTER OUTPUT(2) $T_a=25^\circ\text{C}$



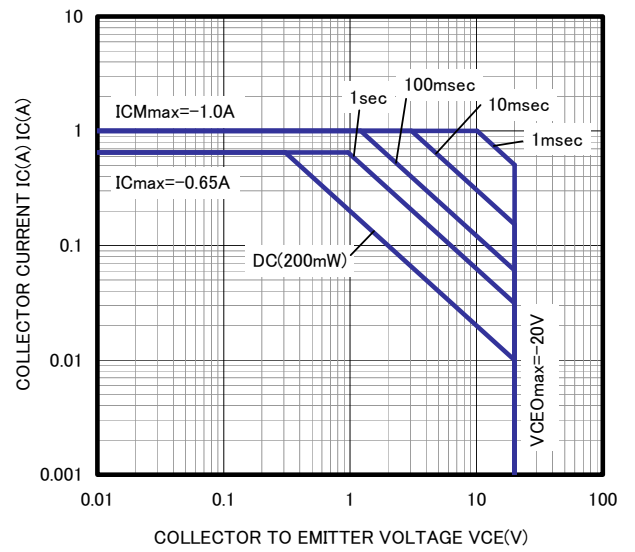
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COLLECTOR TO EMITTER SATURATION VOLTAGE VS.
COLLECTOR CURRENT



AREA OF SAFE OPERATION $T_a=25^\circ\text{C}$
SINGLE PULSE





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